

# **Application Notes: SY6982E**

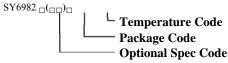
## High Efficiency, 2A, Two-Cell Boost Li-Ion Battery Charger

### **General Description**

SY6982E is a 3.6-5.5V<sub>IN</sub>, 2A two-cell synchronous boost Li-Ion battery charger integrates 1MHz switching frequency and full protection functions. The charge current up to 2A can be programmed by using the external resistor for different portable applications and indicates the charger current information simultaneous. It also has a programmable charge timeout for safety battery charge operation and a programmable input voltage threshold for adaptive input current limit. SY6982E can disconnect output when there is output short circuit or shutdown happens. It consists of 18V rating FETs with extremely low ON resistance to achieve high charge efficiency and simple peripheral circuit design.

SY6982E along with small QFN3x3 footprint provides small PCB area application.

### **Ordering Information**



Ordering Number	Package type	Note
SY6982EQDC	QFN3x3-16	

#### **Features**

Low Profile QFN3x3 Package

Integrated Synchronous Boost with 18V Rating Low  $R_{DSON}$  FETs for High Charge Efficiency Trickle Current / Constant Current / Constant Voltage Charge Mode

Programmable Input Voltage Threshold for Adaptive Current Limit.

Maximum 2A Constant Charge Curre t Charge Current Information Indication. Programmable Charge Timeout

Programmable Constant Charge Current

Selectable Constant Voltage ±0.5% Battery Voltage Accuracy Thermal Regulation Pr tection

External Shutdown Function
Input Voltage UVLO and OVP
Over Temp rature Protection

Output Sho t Circuit Protection Charge St tus Indication

Normal Synchronous Boost Operation When Battery Removed

### **Applications**

Cellular Telephones, PDA, MP3 Players, MP4 Players

Digital Cameras

Bluetooth Applications

PSP Game Players, NDS Game Players Notebook

**Typical Applications** 

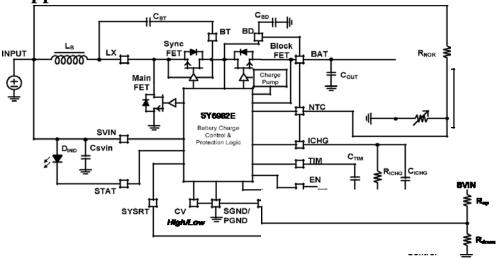
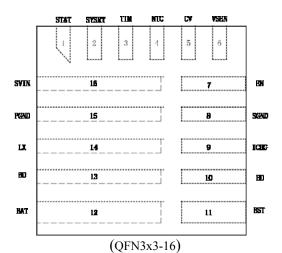


Figure 1. Schematic Diagram



# **Pinout** (top view)



Top Mark: **AWF**xyz, (Device code: AWF, x=year code, y=week code, z= l t number code)

Name	Pin Number	Description				
		Charge status indication pin. It is open drain output pin and pull high to SVIN thru a LEI				
STAT	1	to indicate the charge in process. When the charge is done, LED is off.				
		System ON/OFF control pin. When V <sub>BAT</sub> is lower than 6V, SYSRT pin outputs low logic				
SYSRT	2	to turn off the system operation; when $V_{BAT}$ is high than 6V, SYSRT pin outputs high logic to turn on the system operation.				
		Charge time limit pin. Connect this pin with a capacitor to ground. Internal current source				
TIM	3	charge the capacitor for TC mode and CC mode's charge time limit. TC charge time limit is about 1/9 of CC charge time.				
		Thermal protection pin. UTP hreshold is typical 75%V <sub>SVIN</sub> and OTP threshold is typical				
NTC	4	30%V <sub>SVIN</sub> . Pull up to SVIN can disable charge logic and make the IC operate as normal boost regulator. Pull down to ground can shutdown the IC.				
CV	5	Battery CV voltage selection pin. Program 2 different CV thresholds by setting different				
CV		voltage on the pin. The detailed information is shown in description section.				
		Voltage sense of SVIN. If the voltage drops to internal 1.195V reference voltage, the SVIN will be clamped to setting value and input current will be limited.				
		Enable control pin. High logic for enable on, and low logic for enable off.				
SGND	8	Signal ground pin.				
ICHG	9	Charge current program pin, pull down to GND with a Resistor R <sub>ICHG</sub> . The mirror current about 1/10000 of the blocking FET current will dump into the external RC network thru ICHG pin and compared to the internal reverence 1V. So I <sub>CC</sub> =(1V/R <sub>ICHG</sub> )x10000,				
		I <sub>TC</sub> =(1V/ R <sub>ICHG</sub> )x1000.				
BD	10, 13	Connect to the Drain of internal Blocking FET. Bypass at least 4.7uF ceramic cap to GND.				
BST 11		Boost-Strap pin. Supply Rectified FET's gate driver. Decouple this pin to LX with 0.1uF ceramic cap.				
BAT	12	Battery positive pin.				
LX	14	Switch node pin. Connect to external inductor.				
PGND	15	Power ground pin.				
SVIN  Analog power input pin. Connect a MLCC from this pin to ground to decouple hi harmonic noise. This pin has OVP and UVLO function to make the charger opera within safe input voltage area.						



# **AN\_SY6982E**

<b>Absolute Maximum Ratings</b>	
STAT, NTC, CV, VSEN, EN, ICHG, BD, BAT, LX, SVIN	18V
	4V
SYSRT, TIM, BST-LXLX Pin current continuous	5A
Power Dissipation, PD @ TA = 25°C, QFN3X3	2.6W
Package Thermal Resistance	
$\theta_{JA}$	38°C/W
$ heta_{ m JC}$	4°C/W
Junction Temperature Range	-40°C to +125°C
Lead Temperature (Soldering, 10 sec.)	260°C
Storage Temperature Range	-65°C to 125°C
<b>Recommended Operating Conditions</b>	
SVIN	3.6V to 5.5V
STAT, NTC, CV, VSEN, EN, ICHG, BD, BAT, LX,	
SYSRT, TIM	
LX Pin current continuous	5A
Junction Temperature Range	
Ambient Temperature Range	40°C to 85°C



### **Electrical Characteristics**

 $T_A = 25^{\circ}C, V_{IN} = 5V, GND = 0V, C_{IN} = 4.7 uF, L = 0.68 uH, R_{ICHG} = 10 k\Omega, C_{TIM} = 470 nF, unless otherwise specified.$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Bias Supply						
SVIN	Supply voltage		3.6		16	V
UVLO	svin under voltage lockout threshold	$V_{SVIN}$ rising and measured from $V_{SVIN}$ to GND			3.6	V
UVLO	V <sub>SVIN</sub> under voltage lockout hysteresis	Measured from $V_{SVIN}$ to GND		100		mV
V OVP	Input overvoltage protection	$V_{SVIN}$ rising and measured from $V_{SVIN}$ to GND	5.8			V
OVP	Input overvoltage protection hysteresis	Measured from $V_{SVIN}$ to GND		0.5		V
Quiescent	Current					
BAT	Battery discharge current	Shutdown IC, EN=NTC=0			10	uA
I IN	Input quiescent current	Disable Charge, EN=1,NTC=0			1.5	mA
Oscillator a	and PWM					
SW	Switching frequency			1000		kHz
MINOFF	Main N-FET minimum off time	With 18V rating		100		ns
MAXOFF	Main N-FET maximum off time	With 18V rating		30		us
I MINON	Main N-FET minimum on time	With 18V rating		100		ns
Power MO						
NFET_M	R <sub>DS(ON)</sub> of Main N-FET			80		mΩ
NFET_R	R <sub>DS(ON)</sub> of Rectified N-FET			40		mΩ
NFET_B	R <sub>DS(ON)</sub> of Blocking N-FET			40		mΩ
Voltage Re	gulation					
V		V <sub>CV</sub> <1V	8.358	8.40	8.442	
CV	2-Cell CV charge mode voltage	V <sub>CV</sub> >2V	8.656	8.70	8.743	V
V CVH	High level logic for CV1/2		2			V
CVL	Low level logic for CV1/2				1	V
ΔV RCH	2-Cell Recharge Voltage		100	200	300	mV
TRK	2-cell TC charge mode battery voltage threshold	Rising edge threshold	5.4	5.6	5.8	V
	nnect Detection					
DET	NTC voltage threshold for Battery detect	NTC Falling Edge	85%		95%	V SVIN
t DET	Detect delay time			30		ms
Charge Cu	rrent					
	Internal charge current accuracy for Constant Current Mode	I <sub>CC</sub> =1000mA	-10%		10%	
	Internal charge current accuracy for Trickle Current Mode	I <sub>TC</sub> =100mA	-50%		50%	
TERM	Termination current	I <sub>CC</sub> =1000mA	50	100	150	mA
Output Vo	Itage OVP					
OVP	Output voltage OVP threshold		105%	110%	115%	CV
Input Volta	age Threshold for Adaptive Current L	imit				
V Threshold	Voltage reference of VSEN		1.171	1.195	1.219	V
Timer						



# **AN\_SY6982E**

CC	Output short protection threshold  OFF Control  High logic of system ON/OFF	C <sub>TIM</sub> =330nF	0.23 3.0 1.70	0.5 4.5 30 30 30 30	2.30	hour hour ms ms ms			
MC	Charge mode change delay time Termination delay time Recharge time delay t Protection Output short protection threshold DFF Control High logic of system ON/OFF			30 30 30		ms ms ms			
Term 7 RCHG I Short Circuit SHORT ( System ON/C) V I	Termination delay time Recharge time delay t Protection Output short protection threshold OFF Control High logic of system ON/OFF		1.70	30 30	2.30	ms ms			
Short Circuit Short Circuit SHORT  System ON/C	Recharge time delay t Protection Output short protection threshold OFF Control High logic of system ON/OFF		1.70	30	2.30	ms			
Short Circuit  SHORT  System ON/C  V  I	t Protection Output short protection threshold OFF Control High logic of system ON/OFF		1.70		2.30				
System ON/C	Output short protection threshold  OFF Control  High logic of system ON/OFF		1.70	2.00	2.30				
System ON/C	OFF Control High logic of system ON/OFF		1.70	2.00	2.301	V			
V I	High logic of system ON/OFF				2.50				
	5			1					
HSYSRT	control		2.1			V			
LOVODT	Low logic of system ON/OFF control				0.6	V			
TTTTOOTTO	Hysteresis for positive and negative edge			100		mV			
Linear charg	er Mode								
LCHG I	Battery Charger current when the blocking FET is in linear mode	V V BAT SHORT		5%		CC			
I	Peak linear current when Battery is absent			1		A			
v BD I	Bus voltage regulation		5.8	6	6.2	V			
TRON I	Blocking FET fully turn on hreshold V <sub>TRON</sub> =V <sub>BAT</sub> -V <sub>IN</sub>	V V BAT TRK		100		mV			
Enable ON/O	OFF Control								
v enh I	High level logic for enable control		1.5	Ī		V			
	Low level logic for enable control				0.4	V			
	mal Protection NTC								
	Under temperature protection		70%	75%	80%				
UTP	Under temperature protection	Fall ng edge		5%		V			
	Over temperature protection		28%	30%	32%	SVIN			
OTP (	Over temperature protection	Rising edge		2%		Ì			
Thermal Regulation And Thermal shutdown									
	Thermal regulation threshold	Rising Threshold		120		°C			
$\mathbf{I}$	Thermal regulation hysteresis falling edge	- 0		20		°C			
	Thermal regulation fold back ratio			0.25		CC			
	Thermal shutdown temperature	Rising Threshold		160		°C			
T	Thermal shutdown temperature systeresis	The state of the s		30		°C			

**Note 1**: Stresses be ond the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational s ctions of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note 2:  $\theta_{JA}$  is measured in the natural convection at  $T_A$  = 25°C on a low effective four-layer thermal conductivity test board of JEDEC 51-3 thermal measurement standard.

Note 3: The device is not guaranteed to function outside its operating conditions



## **General Function Description**

SY6982E is a 3.6-5.5V<sub>IN</sub>, 2A two-cell synchronous boost Li-Ion battery charger integrates 1MHz switching frequency and full protection functions. The charge current up to 2A can be programmed by using the external resistor for different portable applications and indicates the charger current information simultaneous. It also has a programmable charge timeout for safety battery charge operation and a programmable input voltage threshold for adaptive input current limit. SY6982E can disconnect output when there is output short circuit or shutdown happens. It consists of 18V rating FETs with extremely low ON resistance to achieve high charge efficiency and simple peripheral circuit design.

#### **Charging Status Indication Description**

- Charge-In-Process Pull and keep STAT pin to Low;
- 2. Charge Done Pull and keep STAT pin to High;
- 3. Fault Mode Output high and low voltage alternatively with 1.3Hz frequency. Connect a LED from SVIN to STAT pin, LED ON means Charge-in-Process, LED OFF means Charge Done, LED Flashing with 1.3HZ means Fault Mode.

# **Switching Mode Boost Charger Basic Operation Description**

#### **Switching Mode Control Strategy**

SY6982E is a switching mode Boost charger for the applications with USB power input. The 1MHz fixed frequency is easy for the size minimization of peripheral circuit design.

#### **Operation Principle**

SY6982E can normally work with or without Li-Ion battery both.

#### **Battery Present**

When the battery is present, SY6982E will works on trickle charging, constant current charging and constant voltage charging mode according to the battery voltage.

#### **Battery Absent**

If there's no battery connection detected thru NTC pin, SY6982E operates as a normal switching mode boost converter. The internal constant current loop and voltage loop are active both.

#### **Basic Protection Principle**

SY6982E has fully battery charging protect on. When the input over voltage protection, the output over voltage protection, the thermal protection or the timeout protection happens, the b st charger stops switching immediately. When the  $V_{BAT}$  is lower than

 $V_{SHORT}$ , the short circuit p otection happens. The main FET is turned off firstly. The block FET enters linear mode with 1/20  $I_{CC}$  charging current. When  $V_{BAT}$  recovers back to be higher than  $V_{SHORT}$ , the boost charger restarts to work at light load and regulates  $V_{BD}$  at 6V. The line charge current is increased from 1/20  $I_{CC}$  to 1/10  $I_{CC}$ . When  $V_{BAT}$  recovers back to be higher than  $V_{SVIN}$ , the boost switching charger takes over.

#### **Adaptive Input Current Limit Principle**

SY6982E can protect the input DC source from over load by the special loop control. The high charging current will caused a voltage drop at SVIN when the input DC source is over load. When VSEN drops below the internal 1.195V reference, SY6982E will decrease the duty cycle to reduce the charging current.

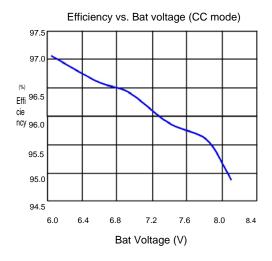
#### **Constant Voltage Threshold Program Principle**

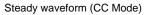
SY6982E can program the constant voltage threshold thru the CV pin. When  $V_{CV}$  is higher than 2V, the constant voltage threshold is 8.7V; when  $V_{CV}$  is lower than 1V, the constant voltage threshold is 8.4V.

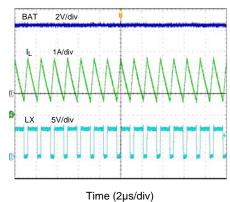


# **Typical Performance Characteristics**

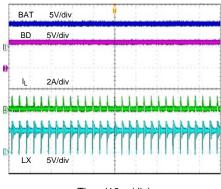
(TA=25°C, VIN=5V, RRCH=10k $\Omega$ , unless otherwise specified. )



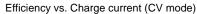


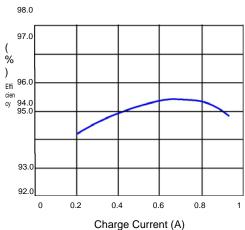


Steady waveform (TC Mode)

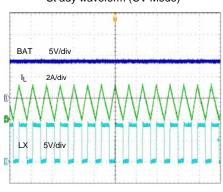


Time (10µs/div)



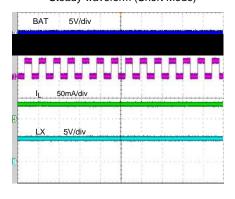


St ady waveform (CV Mode)



Steady waveform (Short Mode)

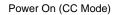
Time (2µs/div)

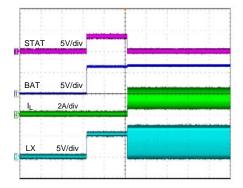


Time (1s/div)



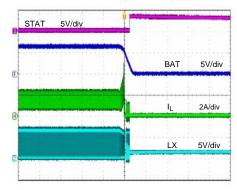
# **AN\_SY6982E**





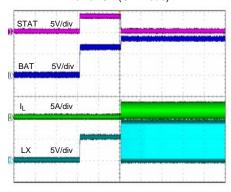
Time (400ms/div)

Power Off (CC Mode)



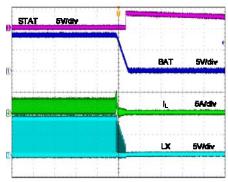
Time (2ms/div)

Power On (CV Mode)



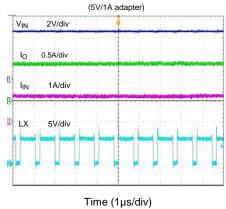
Time (400ms/div)

Power Off (CV Mode)

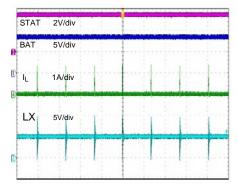


Time (4ms/div)

Adaptive input current limit



Boost Mode (Null load)



Time (20µs/div)



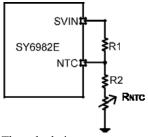
## **Applications Information**

Because of the high integration of SY6982E, the application circuit based on this regulator IC is rather simple. Only input capacitor  $C_{\text{IN}}$ , output capacitor  $C_{\text{OUT}}$ , inductor L, NTC resistors R1,R2, input voltage threshold resistors Rup, Rdown and timer capacitor  $C_{\text{TIM}}$  need to be selected for the targeted applications specifications.

#### NTC resistor:

SY6982E monitors battery temperature by measuring the input voltage and NTC voltage. The controller triggers the UTP or OTP when the rate K (K=  $V_{\rm NTC}/V_{\rm SVIN}$ ) reaches the threshold of UTP (Kut) or OTP (Kot). The temperature sensing network is showed as below.

Choose R1 and R2 to program the proper UTP and OTP points.



The calculation steps are:

- 1. Define  $K_{UT}$ ,  $K_{UT} = 70 \sim 80\%$
- 2. Define Kot, Kot =  $28 \sim 32\%$
- Assume the resistance of the battery NTC thermistor is Rut at UTP threshold a d Rot at OTP threshold
- 4. Calculate R2,

$$R2 = \frac{Kor(1 - Kur)Rut - Kur(1 - Kor)Rot}{Kur - Kor}$$

5. Calculate R1

$$R1 = (1/K_{OT} - 1)(R2 + R_{OT})$$

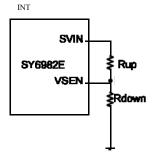
If choose the typical values  $K_{\rm UT}$  =75% and  $K_{\rm OT}\!\!=\!\!30\%,$  then

$$R2 = 0.17R_{UT} - 1.17R_{OT}$$
$$R1 = 2.3(R2 + R_{OT})$$

# Input Voltage Threshold VSEN for Adaptive Current Limit.

SY6982E monitors input voltage by measuring the VSEN voltage, when VSEN drops below the internal 1.195V reference, SY6982E will decrease the duty cycle to reduce the charging current.

The input voltage sense network shows below, choose Rup,Rdown to set the input voltage threshold



$$V_{\text{INT}} = \frac{V_{\text{SEN*}}(R_{\text{down}} + R_{\text{up}})}{R_{\text{down}}}$$
 Unit:V

Vsen is 1.195V.

#### Timer capacitor CTIM

The charger also provides a programmable charge timer. The charge time is programmed by the capacitor connected between the TIM pin and GND. The ca acitance is given by the formula:

acitance is given by the formula: 
$$C_{\text{TIM}} = 2*10^{-11} T_{\text{CC}}$$
 Unit:F

T<sub>CC</sub> is the target constant charge time, unit: s.

#### **Input capacitor Cin:**

The ripple current through input capacitor is greater than

$$\frac{1}{2\sqrt{3} * L*Fsw*Vout}$$

X5R or X7R ceramic capacitors with greater than 4.7uF capacitance are recommended to handle this ripple current.

#### **Output capacitor Cour:**

The output capacitor is selected to handle the output ripple noise requirements. This ripple voltage is related to the capacitance and its equivalent series resistance (ESR). For the best performance, it is recommended to use X5R or better grade low ESR ceramic capacitor. The voltage rating of the output capacitor should be higher than the maximum output voltage. The minimum required capacitance can be calculated as:

$$\frac{= \operatorname{Icc}^*(V_{\text{OUT}} - V_{\text{IN}})}{F_{\text{SW}} \times V_{\text{OUT}} \times V_{\text{RIPPLE}}}$$

 $V_{\mbox{\scriptsize RIPPLE}}$  is the peak to peak output ripple,  $I_{CC}$  is the setting charge current.

For SY6982E, output capacitor is paralleled by  $C_{BD}$  and  $C_{BAT}$ , for smaller output ripple noise, each



capacitor with greater than 10uF capacitance is recommended.

#### **Inductor** L:

There are several considerations in choosing this inductor.

 Choose the inductance to provide the desired ripple current. It is suggested to choose the ripple current to be about 40% of the average input current. The inductance is calculated as:

$$L = \frac{V_{\text{IN}}}{V_{\text{OUT}}} \frac{2}{\text{Icc} \times \text{Fsw} \times 40\%}$$

Where  $F_{SW}$  is the switching frequency and  $I_{CC}$  is the setting charge current.

The SY6982E is quite tolerant of different ripple current amplitude. Consequently, the final choice of inductance can be slightly off the calculation value without significantly impacting the performance.

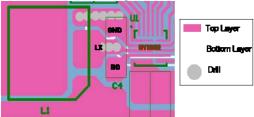
2) The saturation current rating of the inductor must be selected to be greater than the peak inductor current under full load conditions.

3) The DCR of the inductor and the core loss at the switching frequency must be low enough to achieve the desired efficiency requirement. It is desirable to choose an inductor with DCR<10mohm to achieve a good overall efficiency.

#### **Layout Design:**

The layout design of SY6982E regulator is relatively simple. For the best efficiency and minimum noise problems, we should place the following components close to the IC:  $C_{SVIN}$ , L,  $C_{BD}$ .

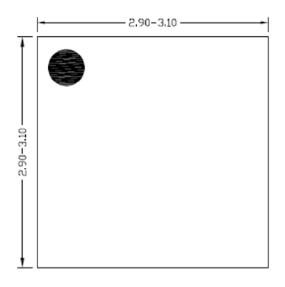
1) The loop of main MOSFET, rectifier diode, and  $C_{BD}$  must be as short as possible

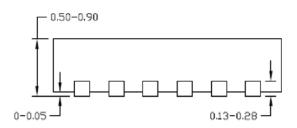


- 2) It is desirable to maximize the PCB copper area connecting to GND pin to achieve the best thermal and noise performance.
- 3) C<sub>SVIN</sub> must be close to pin SVIN and GND.
- 4) The PCB copper area associated with LX pin must be minimized to avoid the potential noise probl m.
- 5) The small signal components  $R_{ICHG}$ , Rup and Rdown must be placed close to IC and must not be adjacent to the LX net on the PCB layout to avoid the noise problem.



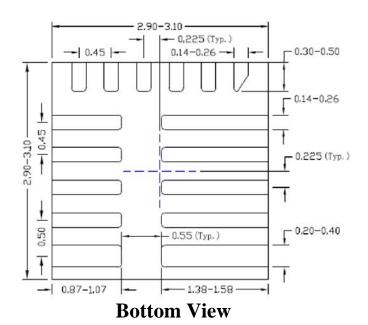
# QFN3x3-16 Package Outline Drawing

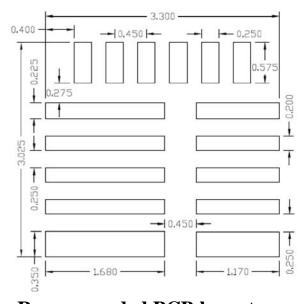




**Top View** 

**Side View** 





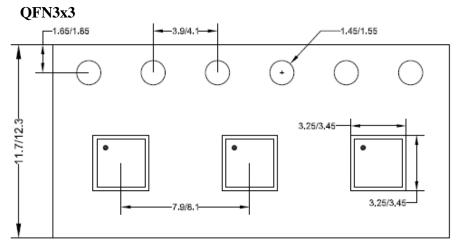
Recommended PCB layout (Reference only)

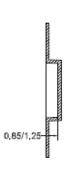
Notes: All dimension in millimeter and exclude mold flash & metal burr



# **Taping & Reel Specification**

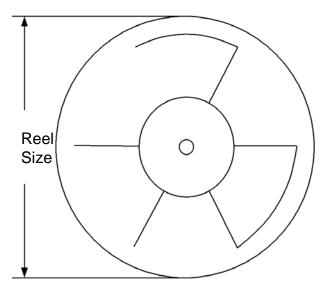
### 1. Taping orientation





Feeding direction ----

## 2. Carrier Tape & Reel specification for packages



Package type	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Trailer length(mm)	Leader length (mm)	Qty per reel
QFN3x3	12	8	13"	400	400	5000

### 3. Others: NA